

# **BUK663R2-40C**

# N-channel TrenchMOS intermediate level FET

Rev. 2 — 14 October 2010

Product data sheet

### 1. Product profile

### 1.1 General description

Intermediate level gate drive N-channel enhancement mode Field-Effect Transistor (FET) in a plastic package using advanced TrenchMOS technology. This product has been designed and qualified to the appropriate AEC Q101 standard for use in high performance automotive applications.

#### 1.2 Features and benefits

- AEC Q101 compliant
- Suitable for intermediate level gate drive sources
- Suitable for thermally demanding environments due to 175 °C rating

### 1.3 Applications

- 12 V Automotive systems
- Electric and electro-hydraulic power steering
- Motors, lamps and solenoid control
- Start-Stop micro-hybrid applications
- Transmission control
- Ultra high performance power switching

### 1.4 Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
$V_{DS}$	drain-source voltage	$T_j \ge 25 ^{\circ}\text{C}; T_j \le 175 ^{\circ}\text{C}$		-	-	40	V
I <sub>D</sub>	drain current	$V_{GS}$ = 10 V; $T_{mb}$ = 25 °C; see <u>Figure 1</u>	[1]	-	-	100	Α
P <sub>tot</sub>	total power dissipation	T <sub>mb</sub> = 25 °C; see <u>Figure 2</u>		-	-	204	W
Static characteristics							
R <sub>DSon</sub>	drain-source on-state resistance	$V_{GS}$ = 10 V; $I_{D}$ = 25 A; $T_{j}$ = 25 °C; see <u>Figure 11</u>		-	2.7	3.2	mΩ



Table 1. Quick reference data ...continued

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Avalanche	ruggedness					
E <sub>DS(AL)S</sub>	non-repetitive drain-source avalanche energy	$I_D$ = 100 A; $V_{sup} \le$ 40 V; $R_{GS}$ = 50 $\Omega$ ; $V_{GS}$ = 10 V; $T_{j(init)}$ = 25 °C; unclamped	-	-	368	mJ
Dynamic c	haracteristics					
$Q_{GD}$	gate-drain charge	$I_D$ = 25 A; $V_{DS}$ = 32 V; $V_{GS}$ = 10 V; see <u>Figure 13</u> ; see <u>Figure 14</u>	-	42	-	nC

<sup>[1]</sup> Continuous current is limited by package.

## 2. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate		
2	D	Drain	mb	D
3	S	source		
mb	D	mounting base; connected to drain		mbb076 S
			SOT404 (D2PAK)	

# 3. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
BUK663R2-40C	D2PAK	plastic single-ended surface-mounted package (D2PAK); 3 leads (one lead cropped)	SOT404

# 4. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
$V_{DS}$	drain-source voltage	T <sub>j</sub> ≥ 25 °C; T <sub>j</sub> ≤ 175 °C		-	40	V
$V_{GS}$	gate-source voltage	Pulsed	<u>[1]</u>	-20	20	V
		DC	[2]	-16	16	V
I <sub>D</sub>	drain current	$T_{mb}$ = 25 °C; $V_{GS}$ = 10 V; see <u>Figure 1</u>	[3]	-	100	Α
		$T_{mb}$ = 100 °C; $V_{GS}$ = 10 V; see <u>Figure 1</u>	[3]	-	100	Α
I <sub>DM</sub>	peak drain current	$T_{mb}$ = 25 °C; $t_p \le 10 \mu s$ ; pulsed; see Figure 3		-	697	Α
P <sub>tot</sub>	total power dissipation	T <sub>mb</sub> = 25 °C; see <u>Figure 2</u>		-	204	W
T <sub>stg</sub>	storage temperature			-55	175	°C
Tj	junction temperature			-55	175	°C
Source-drain	n diode					
Is	source current	T <sub>mb</sub> = 25 °C	[3]	-	100	Α
I <sub>SM</sub>	peak source current	$t_p \le 10 \mu\text{s}; \text{ pulsed}; \text{ T}_{\text{mb}} = 25 ^{\circ}\text{C}$		-	697	Α
Avalanche ru	uggedness					
E <sub>DS(AL)S</sub>	non-repetitive drain-source avalanche energy	$I_D$ = 100 A; $V_{sup}$ ≤ 40 V; $R_{GS}$ = 50 Ω; $V_{GS}$ = 10 V; $T_{j(init)}$ = 25 °C; unclamped		-	368	mJ
E <sub>DS(AL)R</sub>	repetitive drain-source avalanche energy		[4][5][6]	-	-	J

<sup>[1]</sup> Accumulated pulse duration not to exceed 5 mins.

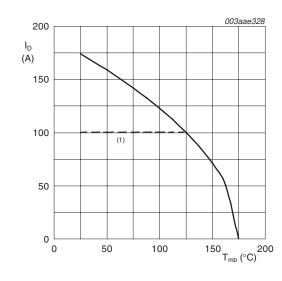
<sup>[2] -16</sup>V accumulated duration not to exceed 168 hrs.

<sup>[3]</sup> Continuous current is limited by package.

<sup>[4]</sup> Single-pulse avalanche rating limited by maximum junction temperature of 175 °C.

<sup>[5]</sup> Repetitive avalanche rating limited by an average junction temperature of 170 °C.

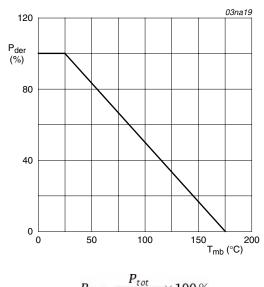
<sup>[6]</sup> Refer to application note AN10273 for further information.



 $V_{GS} \ge 10 \, V$ 

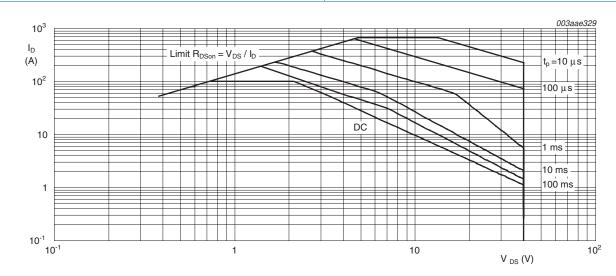
(1) Capped at 100 A due to package.

Continuous drain current as a function of mounting base temperature



$$P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}C)}} \times 100\%$$

Fig 2. Normalized total power dissipation as a function of mounting base temperature



 $T_{mb}$  = 25 °C;  $I_{DM}$  is a single pulse

Fig 3. Safe operating area; continuous and peak drain currents as a function of drain-source voltage

## 5. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base	see Figure 4	-	-	0.74	K/W

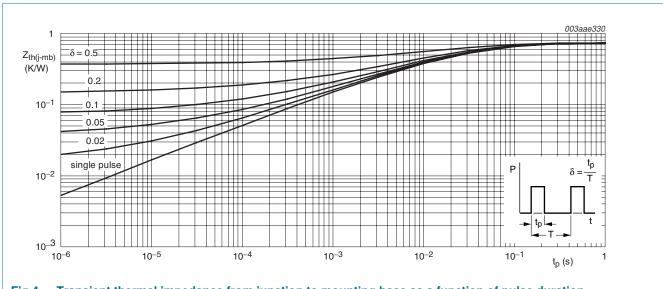


Fig 4. Transient thermal impedance from junction to mounting base as a function of pulse duration

## 6. Characteristics

Table 6. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static cha	racteristics					
V <sub>(BR)DSS</sub>	drain-source	$I_D = 250 \mu A; V_{GS} = 0 V; T_j = 25 °C$	40	-	-	V
,	breakdown voltage	$I_D = 250 \mu A; V_{GS} = 0 V; T_j = -55 °C$	36	-	-	V
()	gate-source threshold voltage	$I_D$ = 1 mA; $V_{DS}$ = $V_{GS}$ ; $T_j$ = 25 °C; see <u>Figure 9</u> ; see <u>Figure 10</u>	1.8	2.3	2.8	V
		$I_D$ = 1 mA; $V_{DS}$ = $V_{GS}$ ; $T_j$ = -55 °C; see <u>Figure 10</u>	-	-	3.3	V
		$I_D$ = 2.5 mA; $V_{DS}$ = $V_{GS}$ ; $T_j$ = 175 °C; see <u>Figure 10</u>	0.8	-	-	V
I <sub>DSS</sub>	drain leakage current	$V_{DS}$ = 40 V; $V_{GS}$ = 0 V; $T_j$ = 175 °C	-	-	500	μΑ
		$V_{DS} = 40 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 ^{\circ}\text{C}$	-	0.02	1	μΑ
I <sub>GSS</sub>	gate leakage current	$V_{DS} = 0 \text{ V}; V_{GS} = 20 \text{ V}; T_j = 25 ^{\circ}\text{C}$	-	2	100	nA
		$V_{DS}$ = 0 V; $V_{GS}$ = -20 V; $T_j$ = 25 °C	-	2	100	nA
Doon	drain-source on-state resistance	$V_{GS}$ = 10 V; $I_{D}$ = 25 A; $T_{j}$ = 25 °C; see <u>Figure 11</u>	-	2.7	3.2	mΩ
		$V_{GS}$ = 5 V; $I_{D}$ = 25 A; $T_{j}$ = 25 °C; see <u>Figure 11</u>	-	3.8	4.8	mΩ
		$V_{GS}$ = 4.5 V; $I_{D}$ = 25 A; $T_{j}$ = 25 °C; see Figure 11	-	4.3	5.7	mΩ
		$V_{GS}$ = 10 V; $I_D$ = 25 A; $T_j$ = 175 °C; see <u>Figure 12</u> ; see <u>Figure 11</u>	-	-	6.7	mΩ
Dynamic	characteristics					
Q <sub>G(tot)</sub>	Q <sub>G(tot)</sub> total gate charge	$I_D$ = 25 A; $V_{DS}$ = 32 V; $V_{GS}$ = 10 V; see <u>Figure 13</u> ; see <u>Figure 14</u>	-	125	-	nC
		$I_D$ = 25 A; $V_{DS}$ = 32 V; $V_{GS}$ = 5 V; see <u>Figure 13</u> ; see <u>Figure 14</u>	-	71	-	nC
$Q_{GS}$	gate-source charge	$I_D = 25 \text{ A}$ ; $V_{DS} = 32 \text{ V}$ ; $V_{GS} = 10 \text{ V}$ ;	-	23	-	nC
$Q_{GD}$	gate-drain charge	see Figure 13; see Figure 14	-	42	-	nC
C <sub>iss</sub>	input capacitance	$V_{GS} = 0 \text{ V}; V_{DS} = 25 \text{ V}; f = 1 \text{ MHz};$	-	6016	8020	pF
Coss	output capacitance	T <sub>j</sub> = 25 °C; see <u>Figure 15</u>	-	739	870	pF
C <sub>rss</sub>	reverse transfer capacitance		-	510	700	pF
t <sub>d(on)</sub>	turn-on delay time	$V_{DS} = 30 \text{ V}; R_L = 1.2 \Omega; V_{GS} = 10 \text{ V};$	-	40	-	ns
t <sub>r</sub>	rise time	$R_{G(ext)} = 10 \Omega$	-	87	-	ns
t <sub>d(off)</sub>	turn-off delay time		-	224	-	ns
t <sub>f</sub>	fall time		-	117	-	ns
L <sub>D</sub>	internal drain inductance	from upper edge of drain mounting base to centre of die; T <sub>j</sub> = 25 °C	-	3.5	-	nΗ
L <sub>S</sub>	internal source inductance	from source lead to source bond pad; T <sub>i</sub> = 25 °C	-	7.5	-	nΗ

Table 6. Characteristics ... continued

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Source-drai	n diode					
$V_{SD}$	source-drain voltage	$I_S$ = 25 A; $V_{GS}$ = 0 V; $T_j$ = 25 °C; see <u>Figure 16</u>	-	8.0	1.2	V
t <sub>rr</sub>	reverse recovery time	$I_S = 20 \text{ A}$ ; $dI_S/dt = -100 \text{ A/}\mu\text{s}$ ; $V_{GS} = 0 \text{ V}$ ;	-	48	-	ns
Q <sub>r</sub>	recovered charge	V <sub>DS</sub> = 25 V	-	82	-	nC

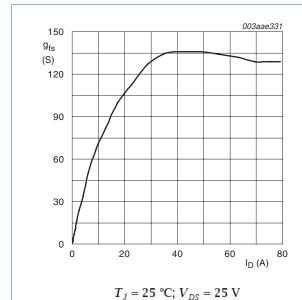


Fig 5. Forward transconductance as a function of drain current; typical values

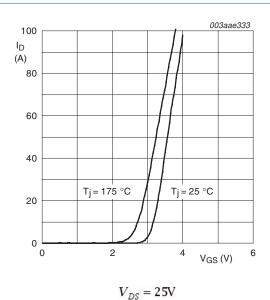
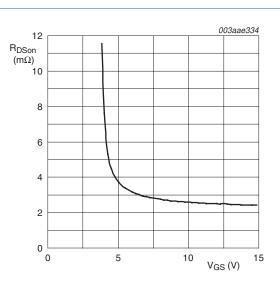


Fig 7. Transfer characteristics: drain current as a function of gate-source voltage; typical values



 $T_j = 25$  °C;  $I_D = 25$  A

Fig 6. Drain-source on-state resistance as a function of gate-source voltage; typical values

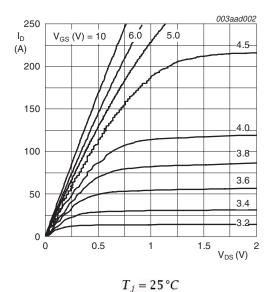


Fig 8. Output characteristics: drain current as a function of drain-source voltage; typical values

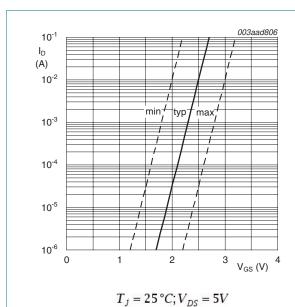


Fig 9. Sub-threshold drain current as a function of gate-source voltage

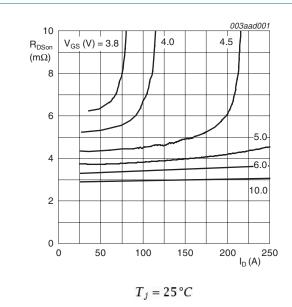
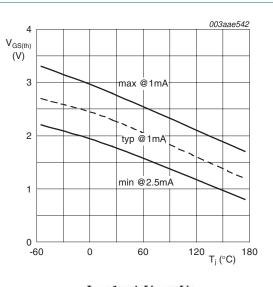


Fig 11. Drain-source on-state resistance as a function of drain current; typical values



 $I_D = 1mA; V_{DS} = V_{GS}$ 

Fig 10. Gate-source threshold voltage as a function of junction temperature

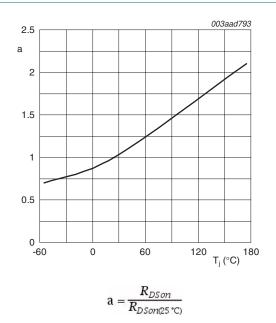


Fig 12. Normalized drain-source on-state resistance factor as a function of junction temperature

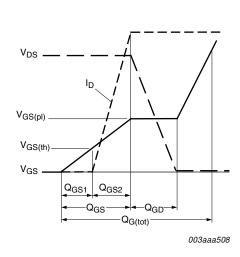
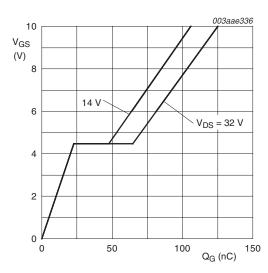


Fig 13. Gate charge waveform definitions



 $T_j = 25 \, ^{\circ}C; I_D = 25 \, A$ 

Fig 14. Gate-source voltage as a function of gate charge; typical values

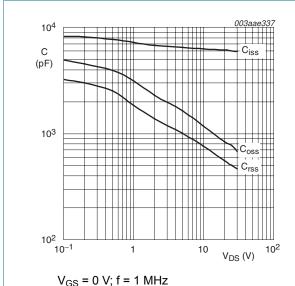
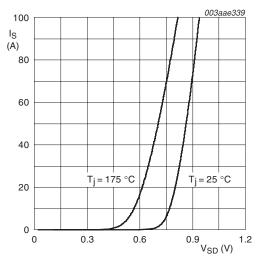


Fig 15. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical

values



 $V_{GS} = 0 V$ 

Fig 16. Source (diode forward) current as a function of source-drain (diode forward) voltage; typical values

## 7. Package outline

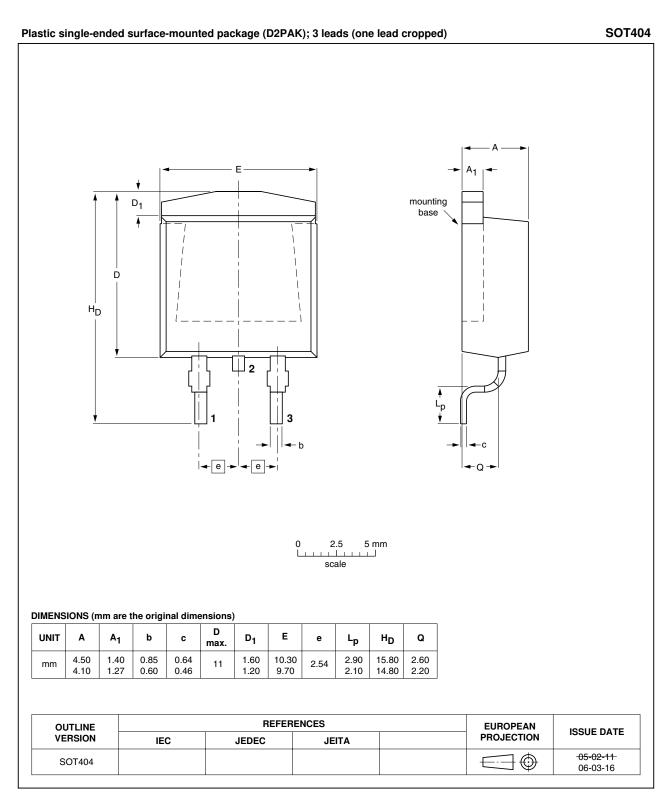


Fig 17. Package outline SOT404 (D2PAK)

# 8. Revision history

### Table 7. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
BUK663R2-40C v.2	20101014	Product data sheet	-	BUK663R2-40C_1
Modifications:	<ul> <li>Status chang</li> </ul>	ed from objective to product.		
BUK663R2-40C_1	20090323	Objective data sheet	-	-

### 9. Legal information

#### 9.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design
- [2] The term 'short data sheet' is explained in section "Definitions"
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# BUK663R2-40C

## **Nexperia**

### N-channel TrenchMOS intermediate level FET

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